



Microwave
Measurement
Techniques

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$$P_n = \left(\frac{v_n}{2R} \right)^2 R = \frac{v_n^2}{4R} = kTB$$

The maximum power delivered from the noisy resistor is $P_n = kTB$, which is considered equally across an entire microwave band.

A resistor temperature at 300^0 k , noise power for a 10kHz bandwidth receiver $\rightarrow P_n = 4.14 \times 10^{-17} \text{ W} = -176\text{dBW} = -146\text{dBm}$

At the standard temperature of 290^0 k , the noise power available from a lossy passive network in a 1Hz bandwidth is -174dBm/Hz .



$$\left. \frac{S}{N} \right|_{dB} = 10 \log \frac{P_s}{P_n} \quad \text{Difficult to measure}$$

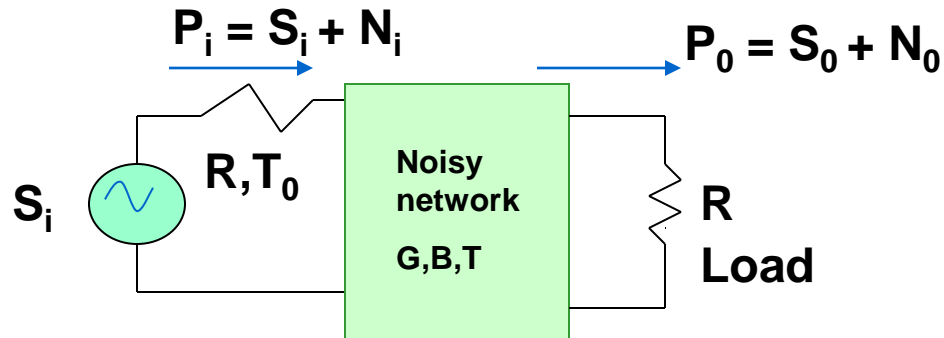
$$\left. \frac{S + N}{N} \right|_{dB} = 10 \log \frac{P_s + P_n}{P_n} \quad \text{Measurable quantity}$$

A receiver produces a noise power of 200mW without signal, as signal is applied, the output level becomes 5W.

$$\left. \frac{S + N}{N} \right|_{dB} = 10 \log \frac{P_s + P_n}{P_n} = 10 \log \frac{5}{0.2} = 14dB$$



A figure of merit to measure the degradation of SNR of a system



$$NF = \frac{(S/N)_i}{(S/N)_o} \geq 1$$

$$NF_{dB} = 10 \log NF \geq 0dB$$

For a passive device with $G=1/L$ and in thermal equilibrium at the temperature T , $N_o = kTB = N_i$, $S_o = GS_i$,

$$NF = \frac{(S/N)_i}{(S/N)_o} = \frac{S_o}{S_i} \frac{N_i}{N_o} = L$$



An amplifier with input signal $100\mu\text{W}$ and the noise power is $1\mu\text{W}$. The amplified signal is 1W with noise power 30mW .

$$\text{signal gain} = 10 \log \frac{1000000}{100} = 40\text{dB}$$

$$\text{noise gain} = 10 \log \frac{30000}{1} = 44.7\text{dB} > 40\text{dB}$$

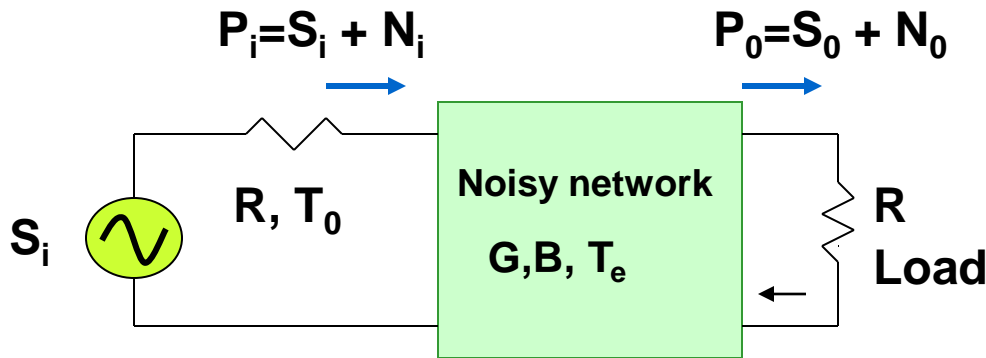
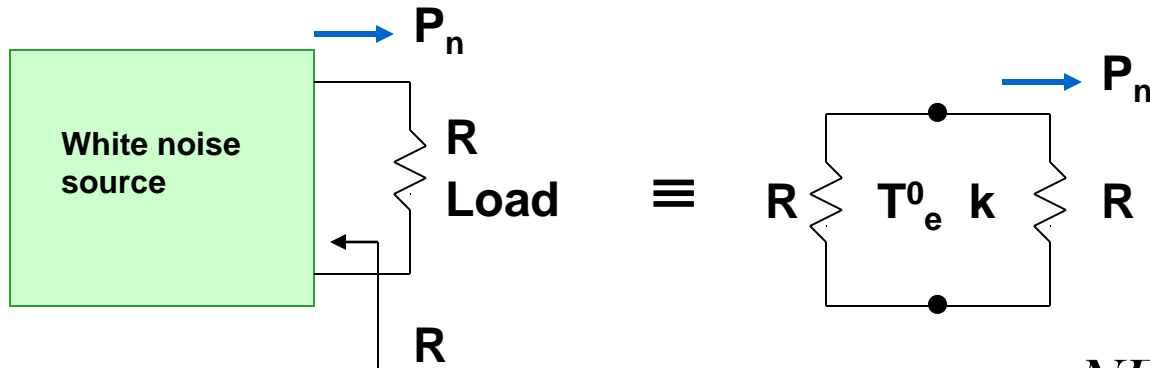
$$NF = \frac{(S/N)_i}{(S/N)_o} = \frac{100/1}{1000/30} = 3 > 1 \quad NF_{dB} = 4.7\text{dB} > 0\text{dB}$$

An amplifier with NF 6dB has an input SNR=40dB,

$$NF = \frac{(S/N)_i}{(S/N)_o} \rightarrow \frac{S}{N_o} \Big|_{dB} = \frac{S}{N_i} \Big|_{dB} - NF_{dB} = 40 - 6 = 34\text{dB}$$



Equivalent noise temperature: the absolute temperature to generate the same noise power, not the physical temperature of the device equivalent noise temperature $T_e \equiv P_n / kB$



$$\begin{aligned}
 NF &= \frac{(S/N)_i}{(S/N)_o} \\
 &= \frac{S_i}{kT_0 B} \frac{Gk(T_0 + T_e)}{GS_i} B \\
 &= 1 + \frac{T_e}{T_0} \geq 1 \\
 \rightarrow T_e &= (NF - 1)T_0
 \end{aligned}$$



$$NF = \frac{(S/N)_i}{(S/N)_o} = \frac{S_i N_0}{S_0 N_i}$$

$$= \frac{1}{\prod_{i=1}^N G_i} \left\{ \frac{kT_0 B \prod_{i=1}^N G_i}{kT_0 B} + \frac{k(NF_1 - 1)T_0 B \prod_{i=1}^N G_i}{kT_0 B} + \frac{k(NF_2 - 1)T_0 B \prod_{i=2}^N G_i}{kT_0 B} + \dots + \frac{k(NF_N - 1)T_0 B G_N}{kT_0 B} \right\}$$

A three-stage amplifier

Stage	power gain	noise figure
1	10 10dB	2 3dB
2	20 13dB	4 6dB
3	30 14.8dB	6 7.8dB

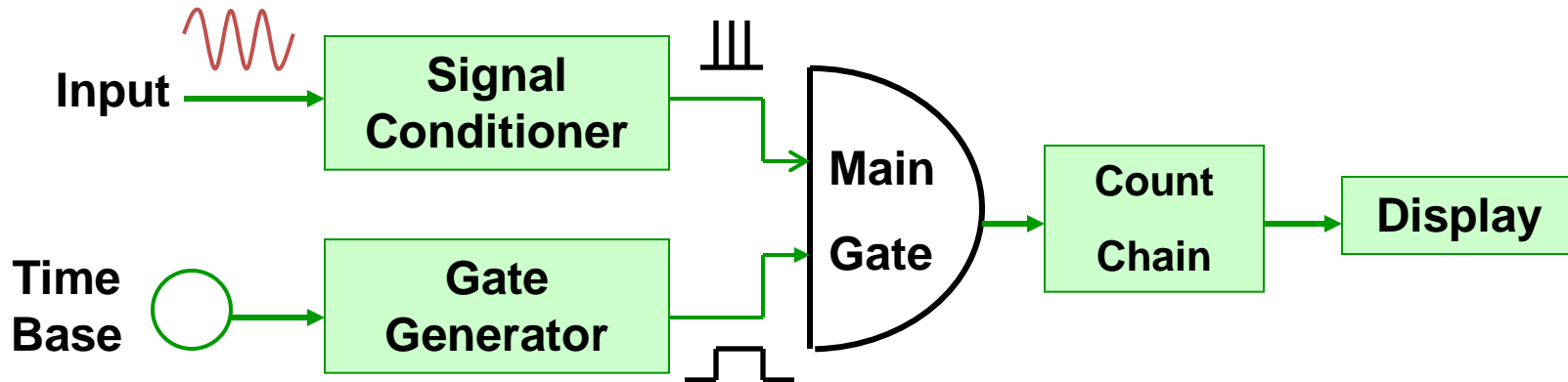
Total gain=6000=37.8dB

Total NF=2+[(4-1)/10]+[(6-1)/(10×20)]=2.325=3.66dB

Two approaches: using frequency counter to measure frequency directly, and using probe to measure the wavelength in a transmission line.

Frequency counter approach

(1) Basic principle: direct counting <500MHz

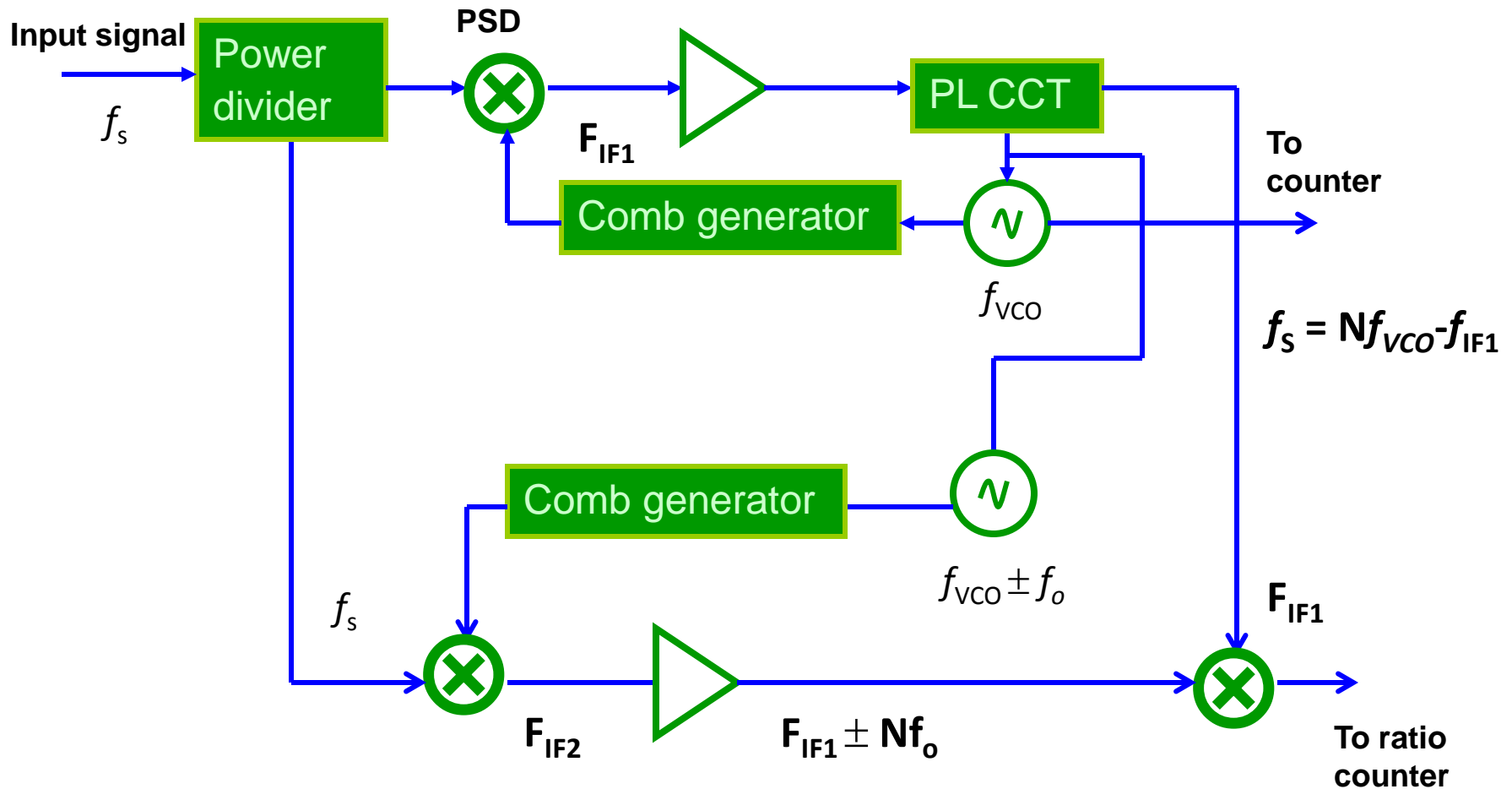


(2) Using frequency down-conversion techniques for microwave signals

- Pre-scaling: divider circuit <2GHz

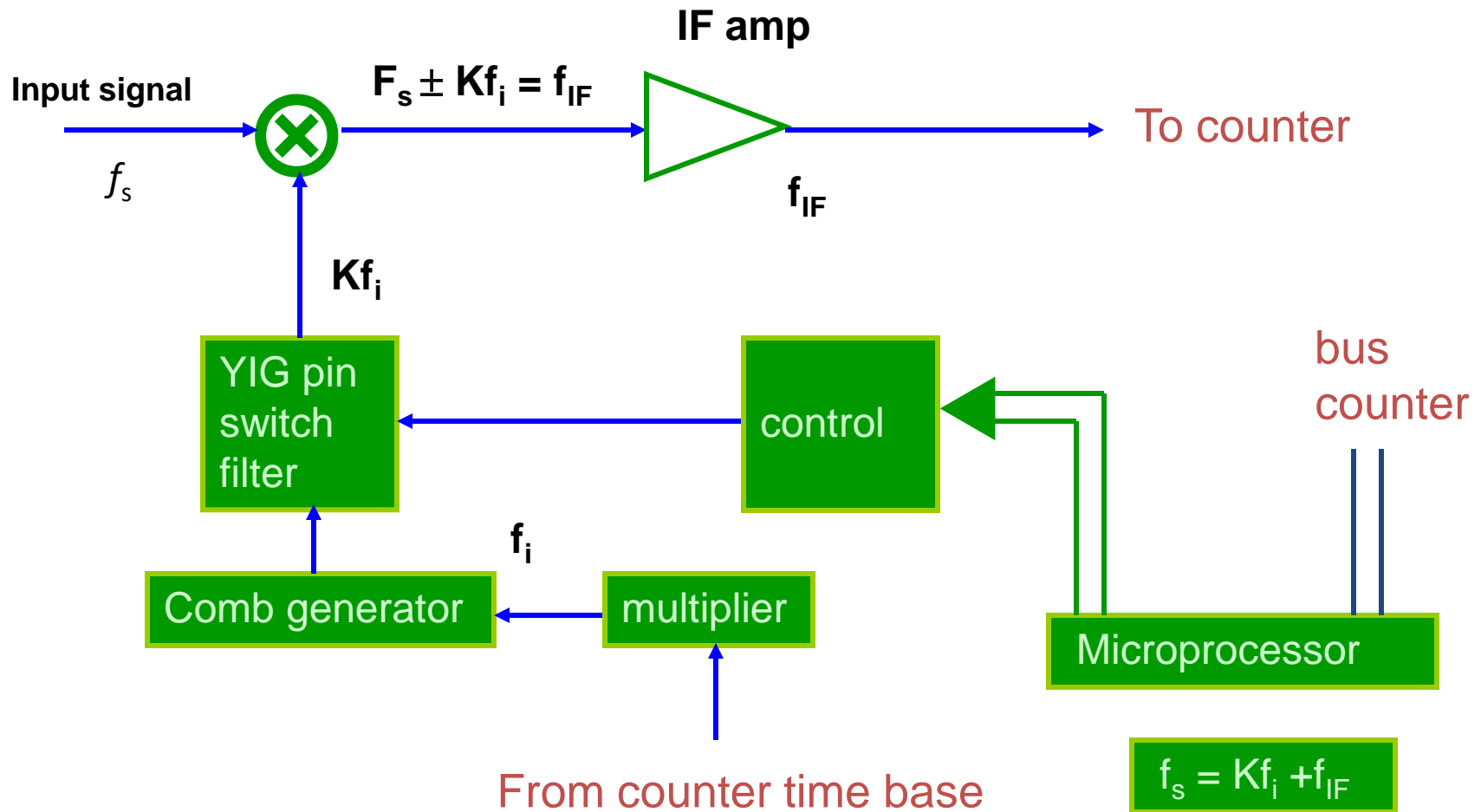


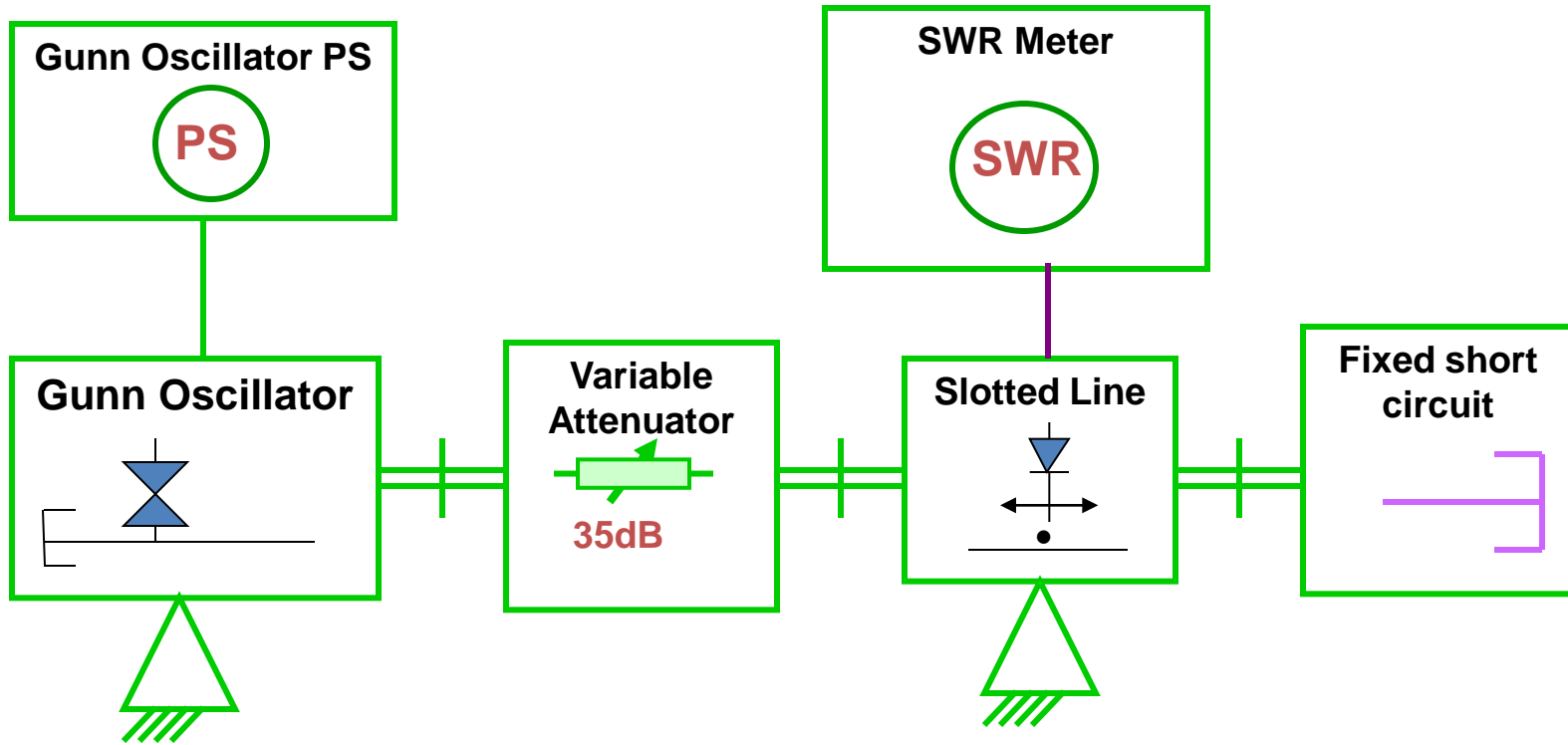
- Transfer oscillator down-conversion: use PLL to relate the harmonic relationship between the low frequency oscillator and the input microwave signal $> 40\text{GHz}$





Harmonic heterodyne: use mixer to harmonically down convert the input microwave signal $<20\text{GHz}$





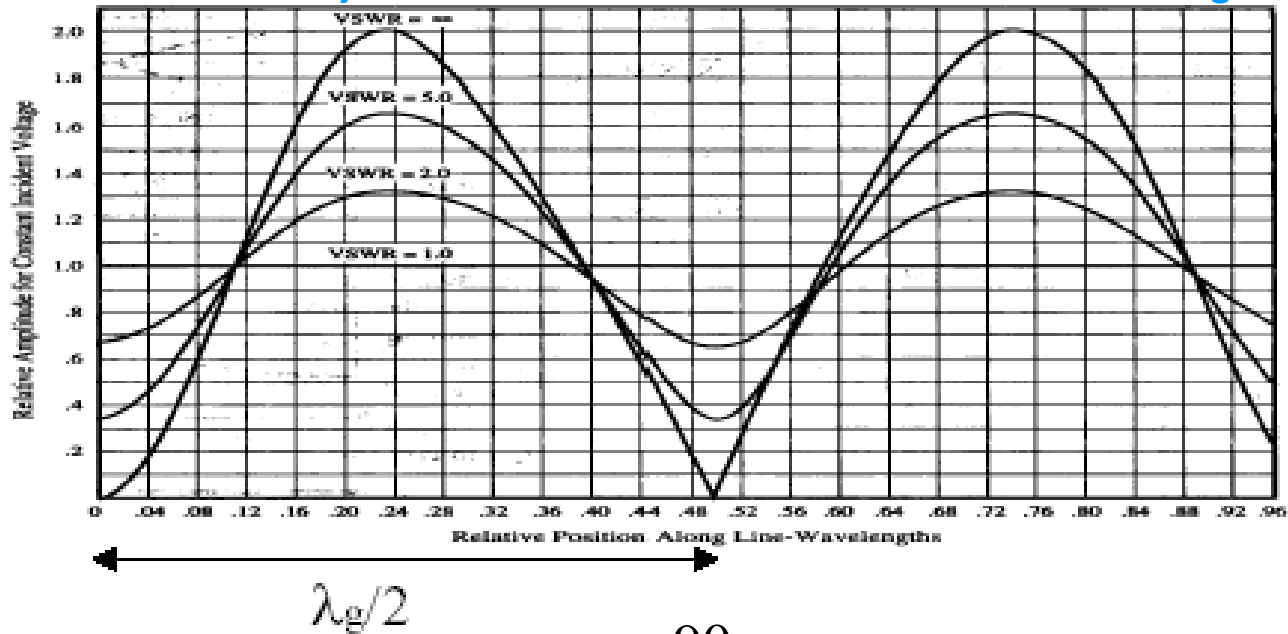
$$k_c = \frac{2\pi}{\lambda_c}, \lambda_c = 2a, \beta = \frac{2\pi}{\lambda_g} = \sqrt{k^2 - k_c^2} = \sqrt{\left(\frac{2\pi}{\lambda}\right)^2 - \left(\frac{2\pi}{\lambda_c}\right)^2}$$

Measure

$$\lambda_g \rightarrow f = c \sqrt{\left(\frac{1}{\lambda_g}\right)^2 + \left(\frac{1}{2a}\right)^2}$$



Distance between two adjacent minima is 1.9cm in a WR-90 waveguide.

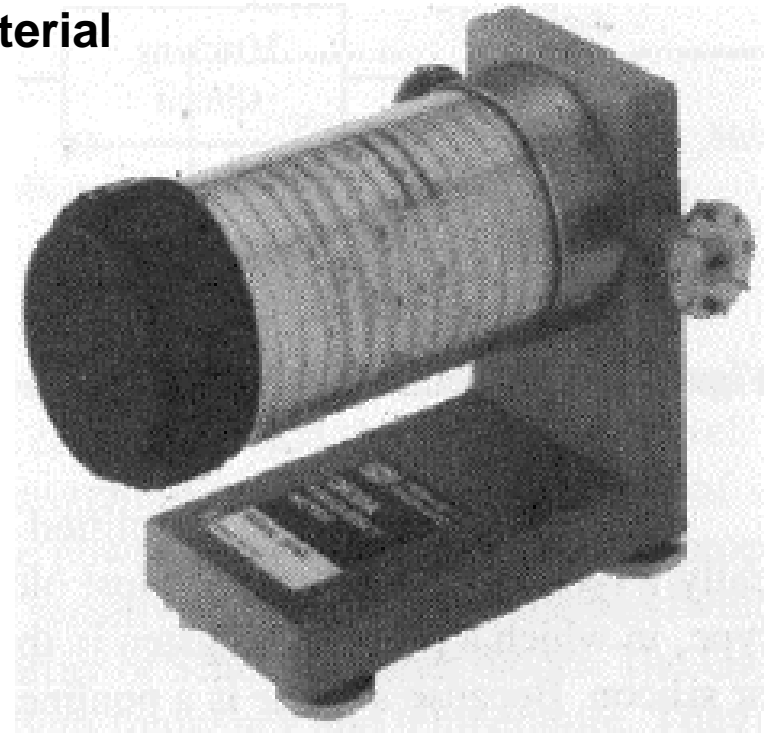
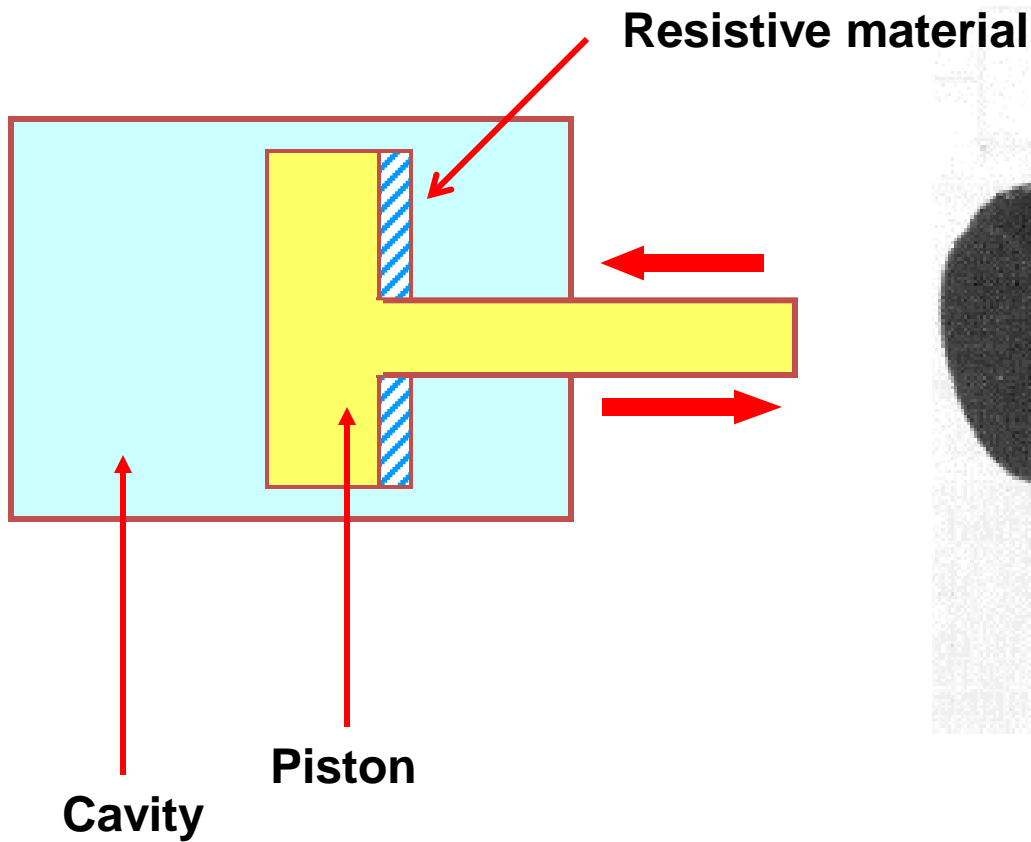


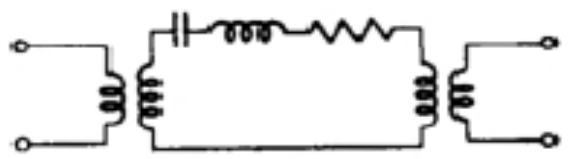
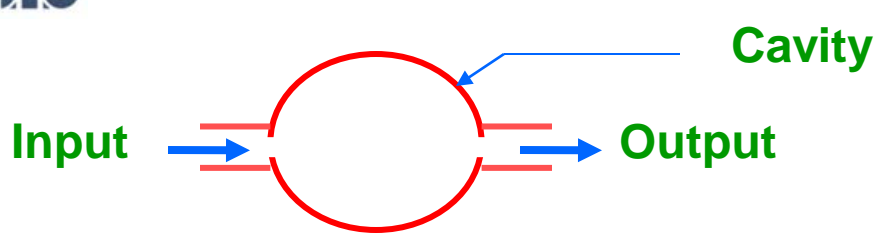
$$\lambda_g = 2 \times 1.9 \text{ cm} = 3.8 \text{ cm}, \quad a = \frac{90}{100} \times 2.54 \text{ cm} = 2.29 \text{ cm}$$

$$f = c \sqrt{\left(\frac{1}{\lambda_g}\right)^2 + \left(\frac{1}{2a}\right)^2}$$

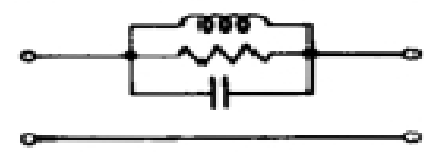
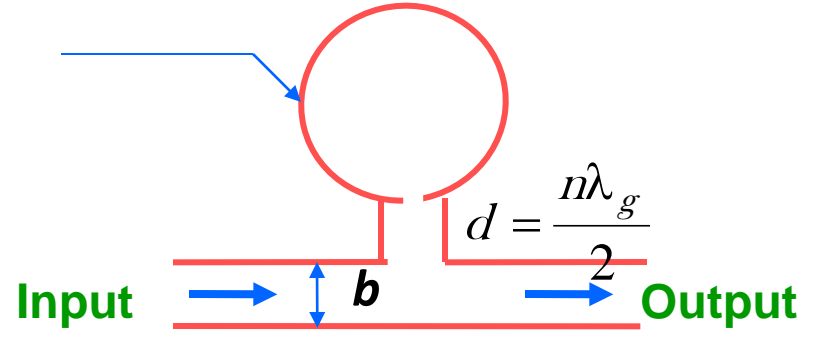
$$= 3 \times 10^{10} \text{ cm/sec} \sqrt{\left(\frac{1}{3.8 \text{ cm}}\right)^2 + \left(\frac{1}{2 \times 2.29 \text{ cm}}\right)^2} = 10.26 \text{ GHz}$$

▪ Wavemeter structure



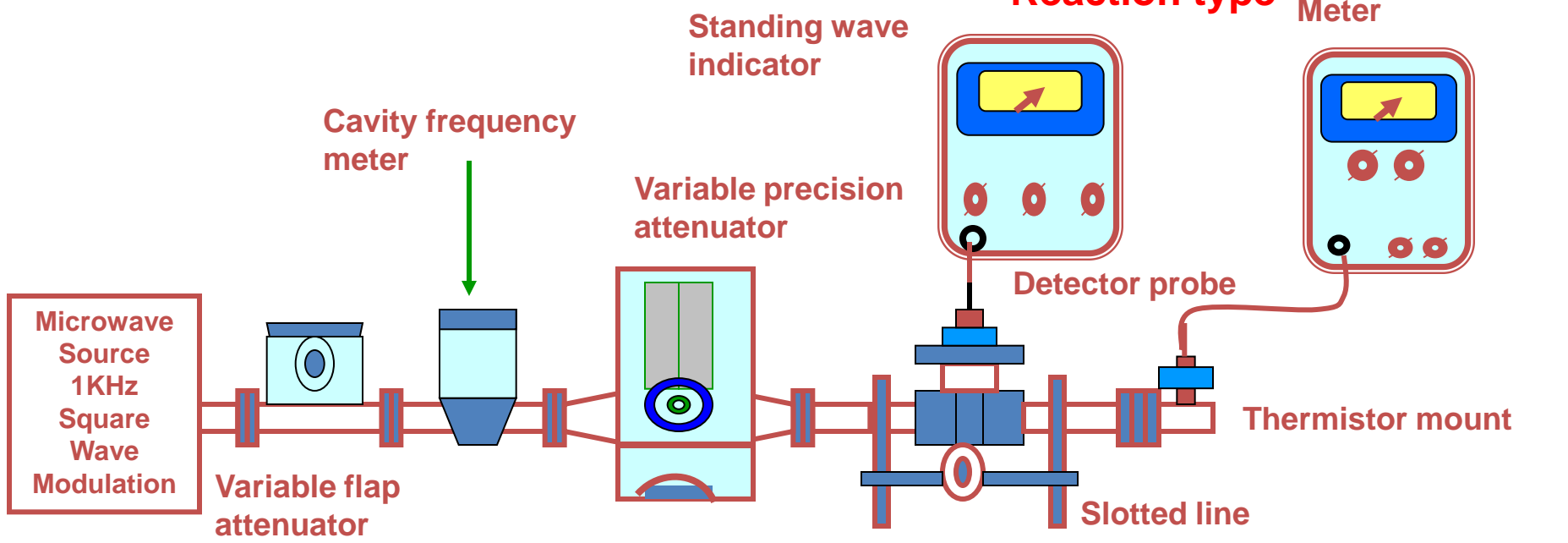


Transmission type



Reaction type

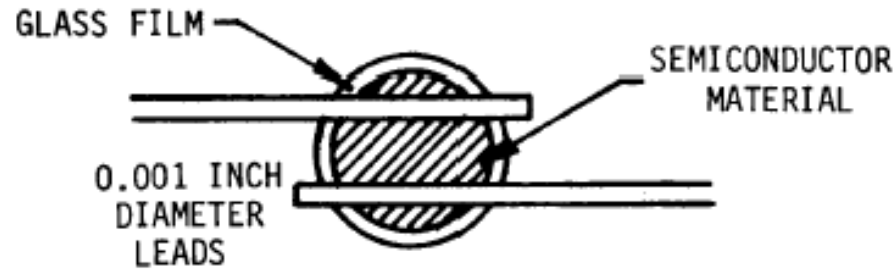
Microwave Power Meter



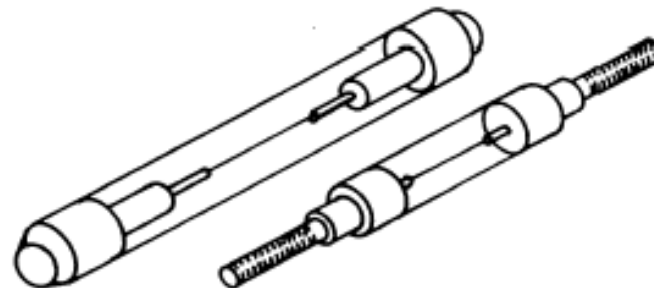


Power detector: bolometer (thermistor and barretter), thermocouple voltage detector: crystal detector, Schottky barrier diode, GaAs barrier diode

Thermistor: a metallic-oxide component with a negative temperature coefficient of resistance



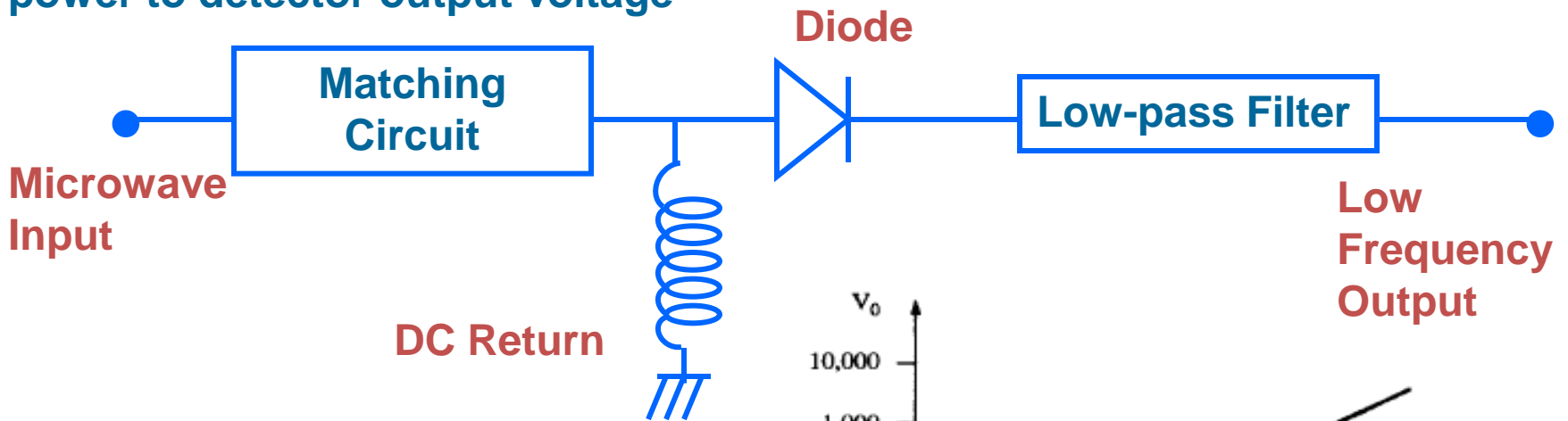
Barretter: a short length of platinum or tungsten wire with a positive temperature coefficient of resistance



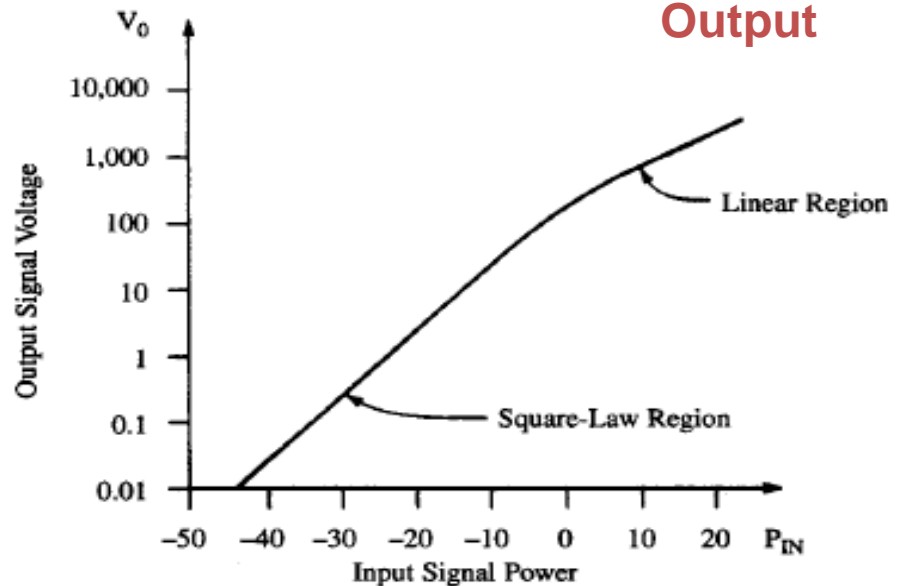


Thermocouple: a pair of dissimilar metal (Sb-Bi) wires joined at one end (sensing end) and terminated at the other end (reference end). The difference in temperature produces a proportional voltage.

Crystal detector: use the diode square-law to convert input microwave power to detector output voltage



DC return is as a ground for diode and an RF choke.





Schottky barrier or GaAs barrier diode: high sensitivity noise equivalent power (NEP): the required input power to produce, in 1Hz bandwidth, an output SNR = 1 tangential sensitivity (TSS): the lowest detectable microwave signal power

$$NEP = \frac{TSS}{2.5\sqrt{\Delta f}}, \Delta f : \text{Video Bandwidth}$$

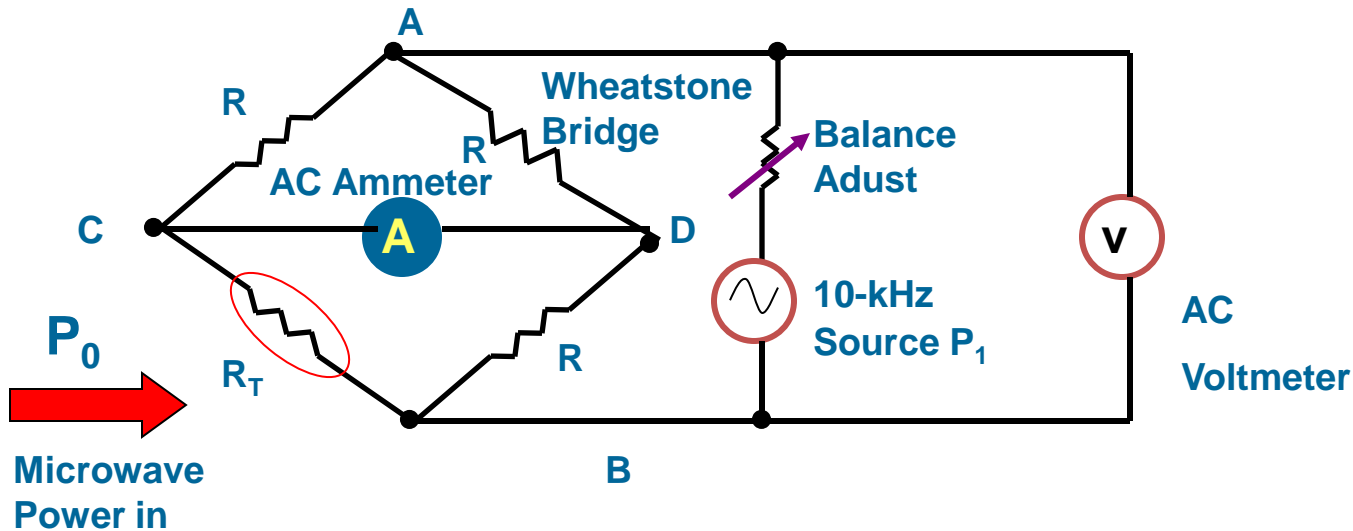
Characteristics	Crystals	Barretters	Thermistors
Response Time	Extremely fast	≈ 350 μs	≈ 1 sec
Square-law Response	≈ 10 μW	≈ 200 μW	≈ 200 μW
Resistance to Burnout	Determined by design	≈ 12 mW	≈ 25 mW
Resistance to Shock	Poor	Fair	Good
Temperature Coefficient	None	Positive	Negative
Minimum Discernable Signal	$1.8 \times 10^{-6} \mu\text{W}$	$1.0 \times 10^{-4} \mu\text{W}$	$1.0 \times 10^{-4} \mu\text{W}$
Method of Operation	Rectifies Voltage	Absorbs EM energy	Absorbs EM energy

Difficulty in measuring voltage or current at microwave frequencies
 → power measurement simpler and more precise

Power range: low power <0dBm, medium power 0dBm~40dBm, high power >40dBm

power detector sensitivity: diode ~-70dBm, thermistor ~-20dBm

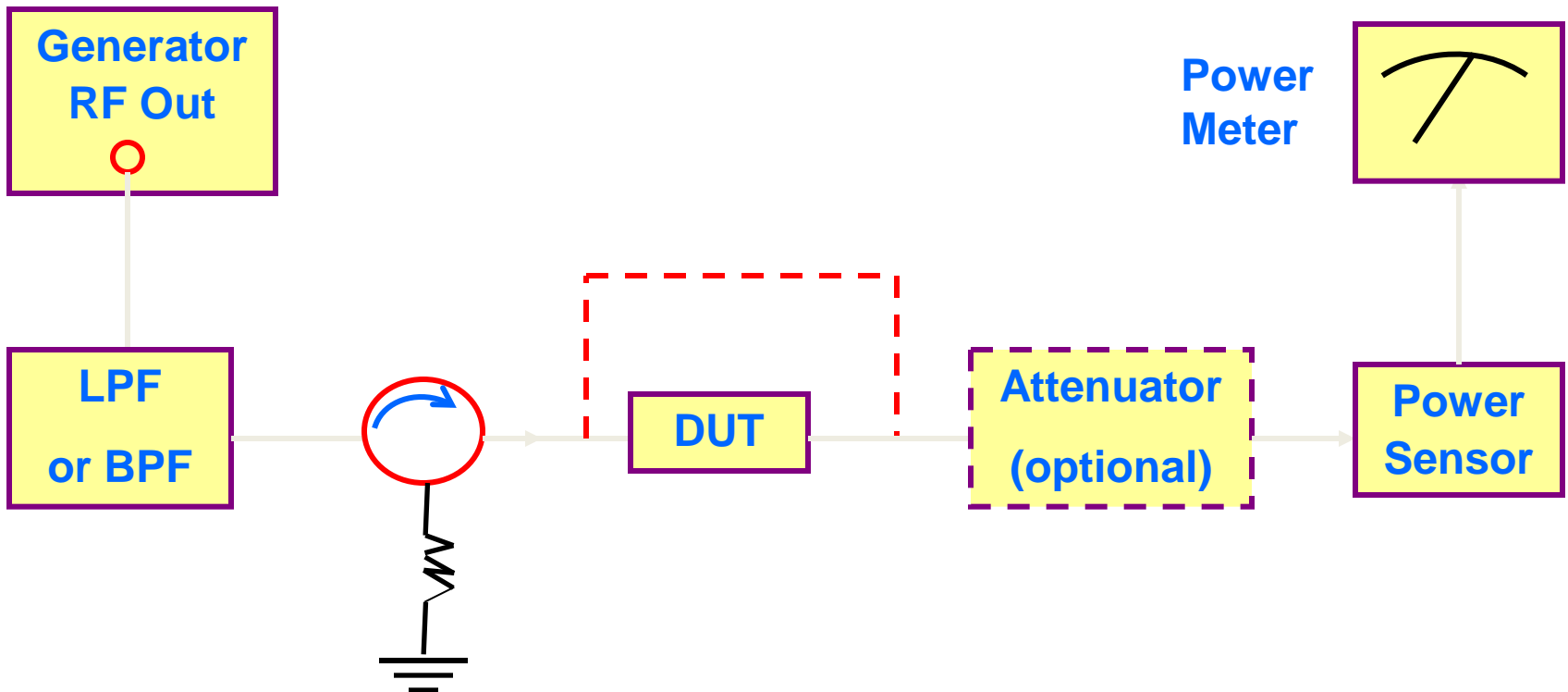
Thermistor power meter





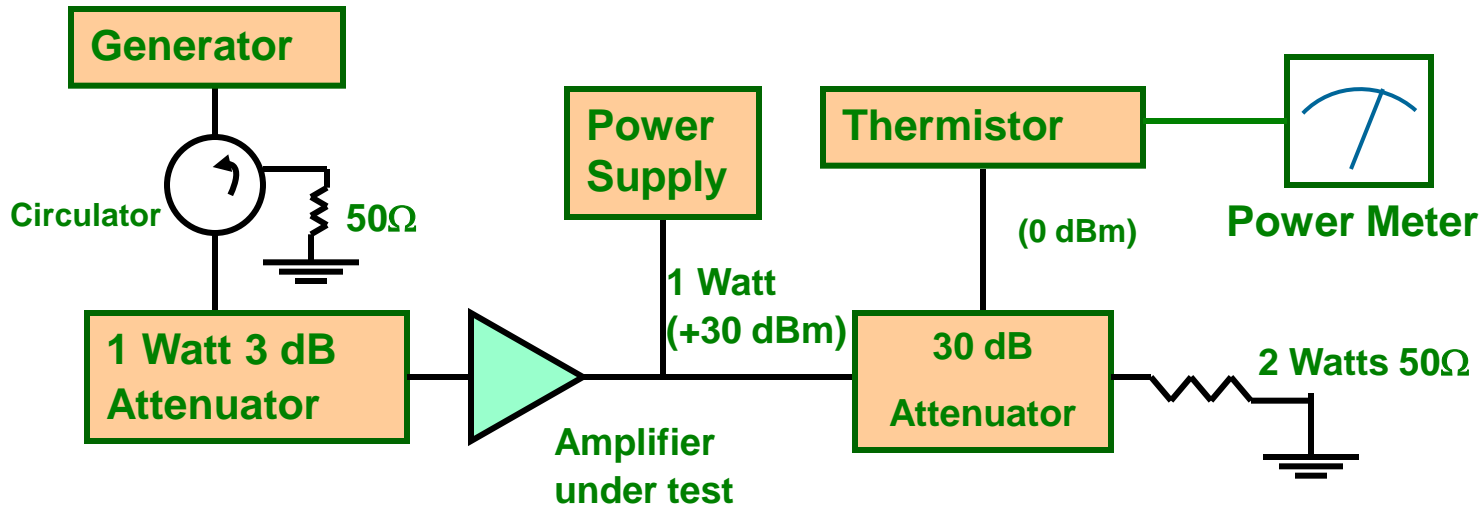
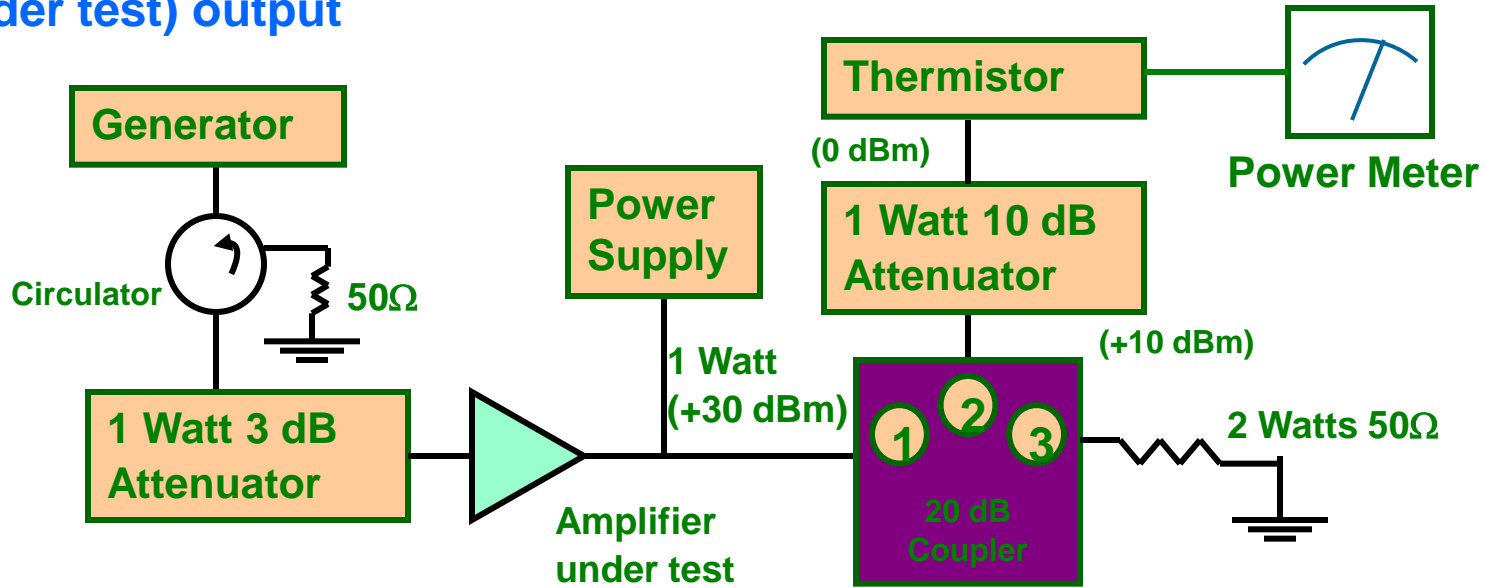
• Low power case

Consider desired frequency spectrum, circuit mismatch, sensor mismatch, sensor safe margin, accuracy, calibration



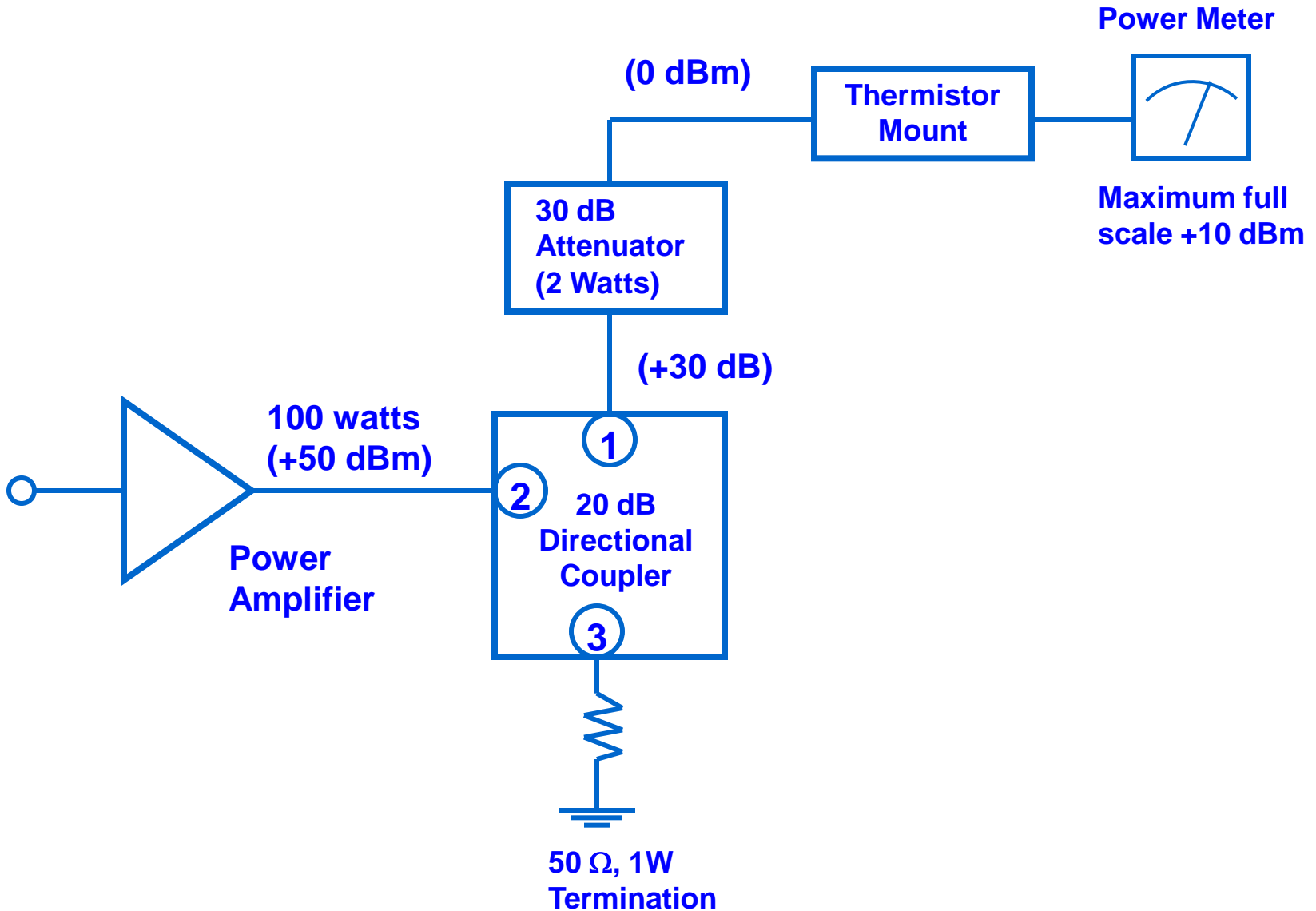


Medium power case: use directional coupler or attenuator at the DUT (device under test) output



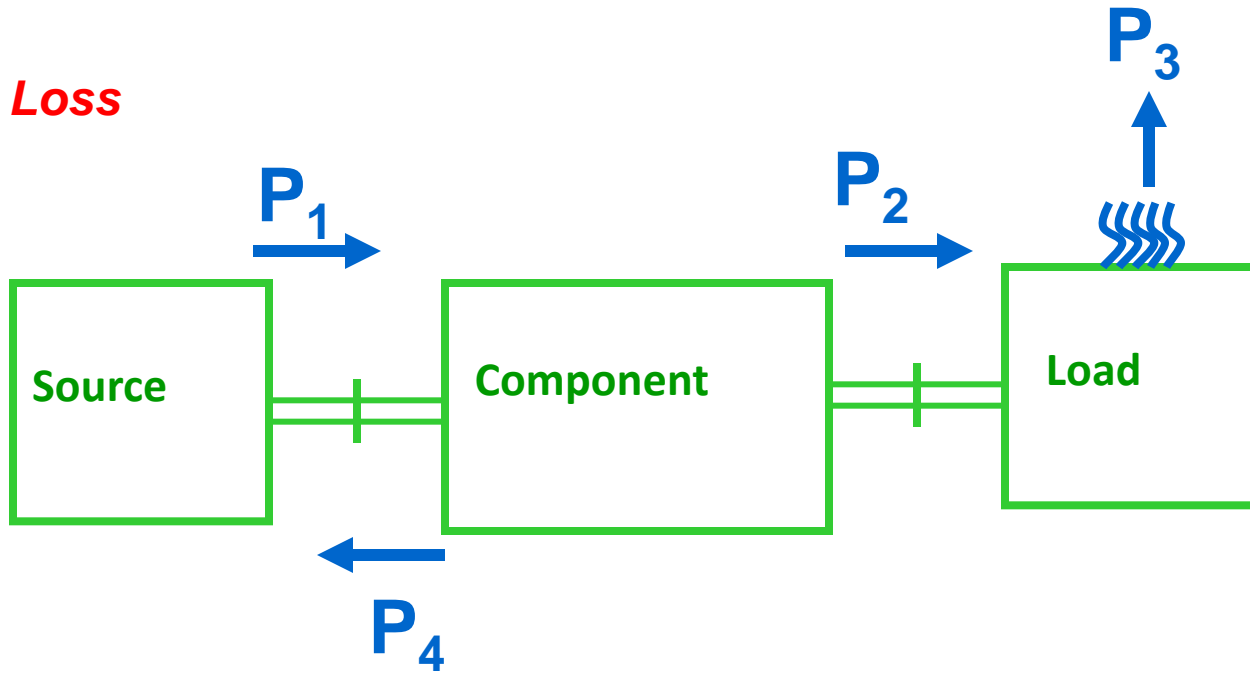


High power case: use directional coupler in reverse direction





Insertion Loss



P1: power to the load without DUT

P2: power to the load after inserting DUT

P3: power dissipated inside DUT

P4: power reflected from DUT

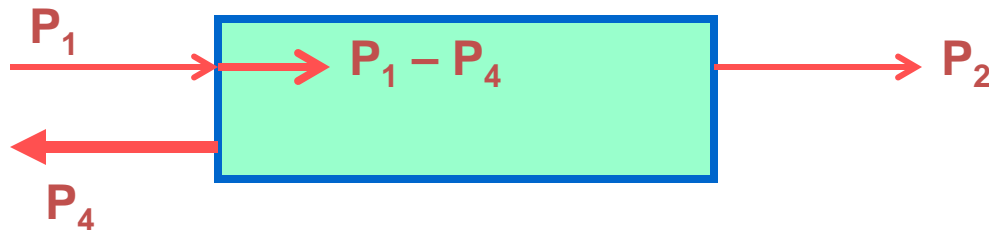
$$IL_{dB} = 10 \log \frac{P_1}{P_2} = P_{1(dBm)} - P_{2(dBm)}$$



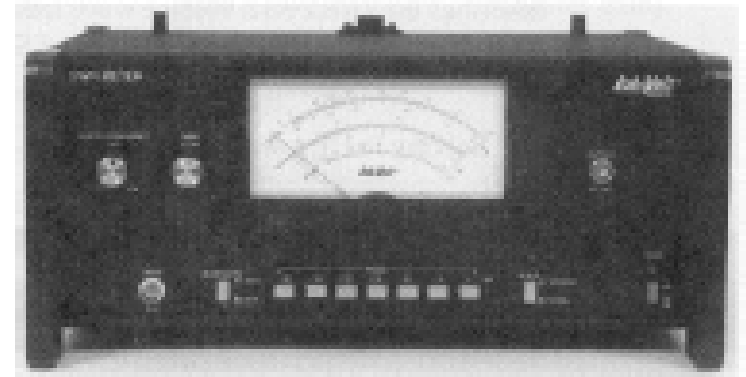
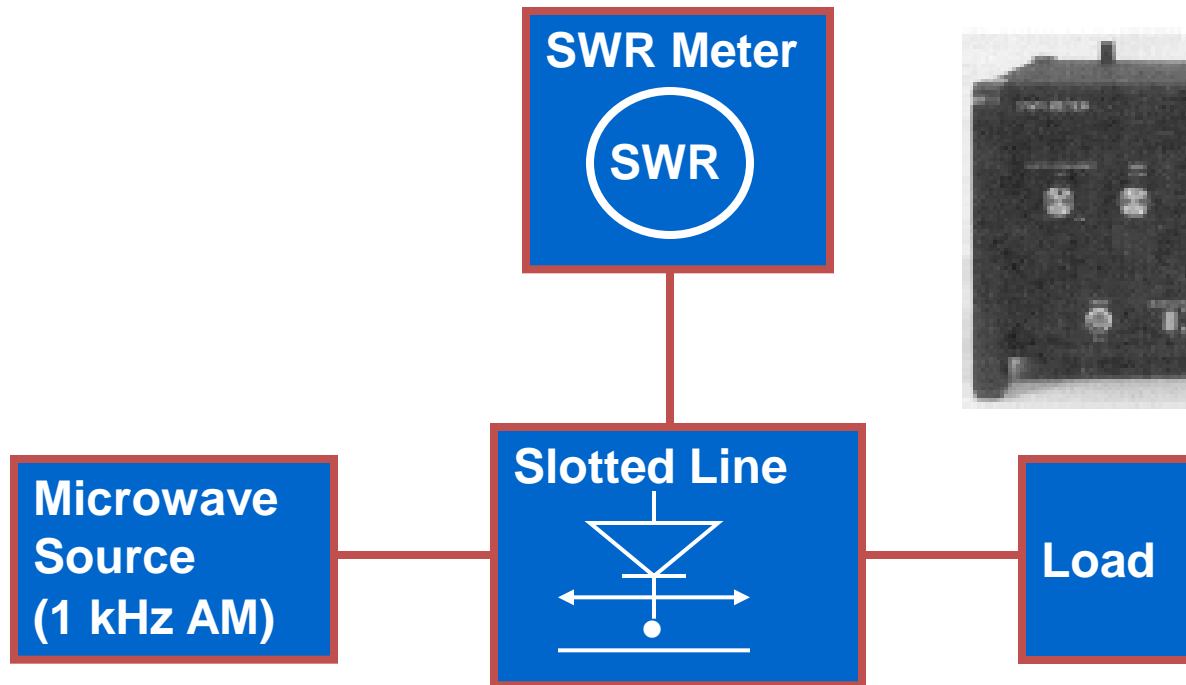
If Γ : DUT reflection coefficient and T: DUT transmission coefficient,

$$\begin{aligned} IL_{dB} &= -10 \log |T|^2 = -10 \log |T|^2 \frac{1 - |\Gamma|^2}{1 - |\Gamma|^2} \\ &= -10 \log (1 - |\Gamma|^2) - 10 \log \frac{|T|^2}{1 - |\Gamma|^2} \\ &= -10 \log \frac{P_1 - P_4}{P_1} - 10 \log \frac{P_2}{P_1 - P_4} \end{aligned}$$

= loss due to reflection + loss due to transmission



Insertion loss is the characteristics of DUT itself. As input port and output ports are matched, IL= attenuation.



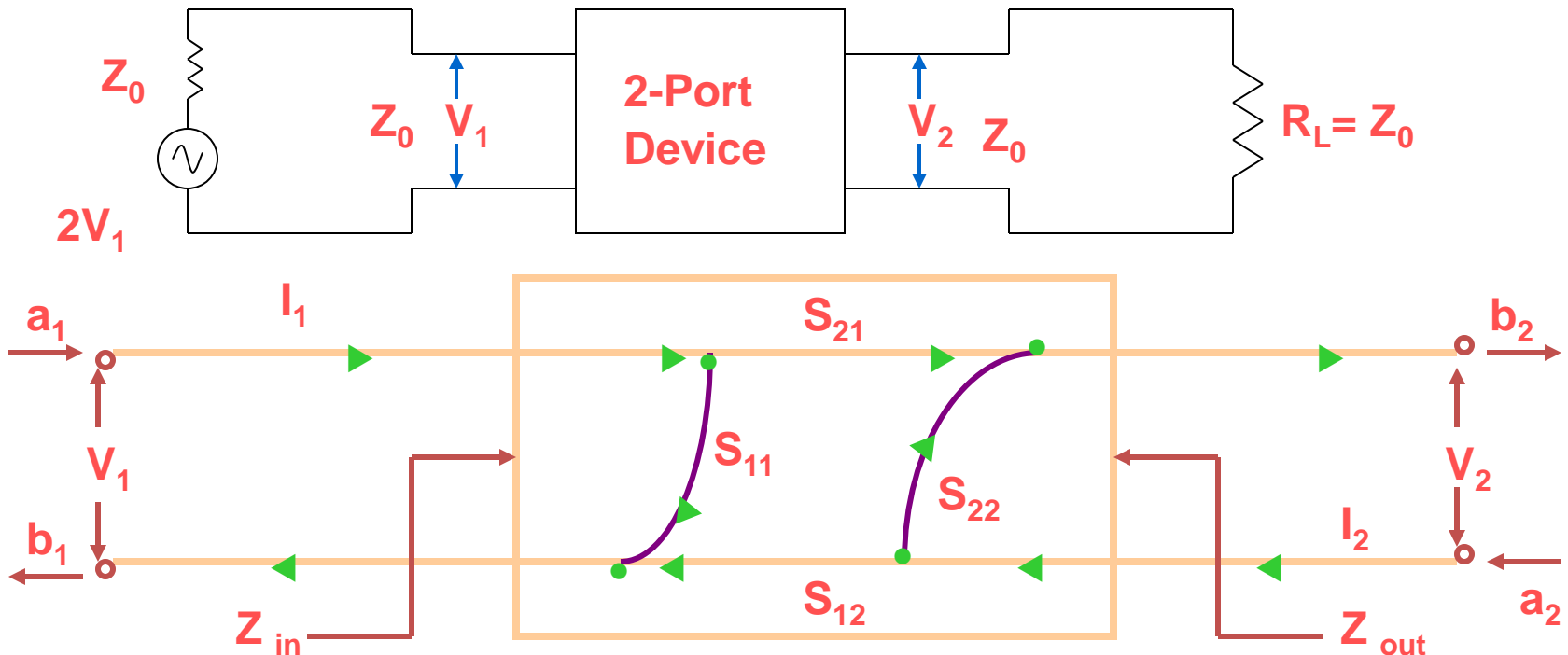
If E probe penetrates too far into the slotted line, → disturb the field distribution and detected signal too strong to drive the detector out of its square-law region.



Problems to use Z-, Y- or H- parameters in microwave circuits

- Difficult in defining voltage and current for non-TEM lines
- No equipment available to measure voltage and current in complex value as oscilloscope
- Difficult to make open and short circuits over broadband
- Active devices not stable as terminated with open or short circuit.

S-parameters of a two-port network





$$a_1 = V_1^+ / \sqrt{Z_0}$$

: incident (power) wave at port 1

$$b_1 = V_1^- / \sqrt{Z_0}$$

: reflected (power) wave at port 1

$$a_2 = V_2^+ / \sqrt{Z_0}$$

: incident (power) wave at port 2

$$b_2 = V_2^- / \sqrt{Z_0}$$

: reflected (power) wave at port 2

$$V_1 = V_1^+ + V_1^-, V_2 = V_2^+ + V_2^-, I_1 = \frac{V_1^+}{Z_0} - \frac{V_1^-}{Z_0}, I_2 = \frac{V_2^+}{Z_0} - \frac{V_2^-}{Z_0}$$

$$\begin{bmatrix} b_1 \\ b_2 \end{bmatrix} = \begin{bmatrix} S_{11} & S_{12} \\ S_{21} & S_{22} \end{bmatrix} \begin{bmatrix} a_1 \\ a_2 \end{bmatrix}, S_{ij} = \left. \frac{b_i}{a_j} \right|_{a_i=0, k \neq j} = \left. \frac{V_i^-}{V_j^+} \right|_{V_k^+ = 0, k \neq j}$$

➡ Incident power to port i :

$$P_i = \frac{1}{2} \Re \left\{ V_i I_i^* \right\} = \frac{1}{2} |a_i|^2 - \frac{1}{2} |b_i|^2$$



$$S_{11} = \left. \frac{b_1}{a_1} \right|_{a_2=0}$$

: reflection coefficient at port 1 with port 2 matched

$$S_{21} = \left. \frac{b_2}{a_1} \right|_{a_2=0}$$

: forward transmission coefficient with port 2 matched

$$S_{12} = \left. \frac{b_1}{a_2} \right|_{a_1=0}$$

: reversed transmission coefficient with port 1 matched

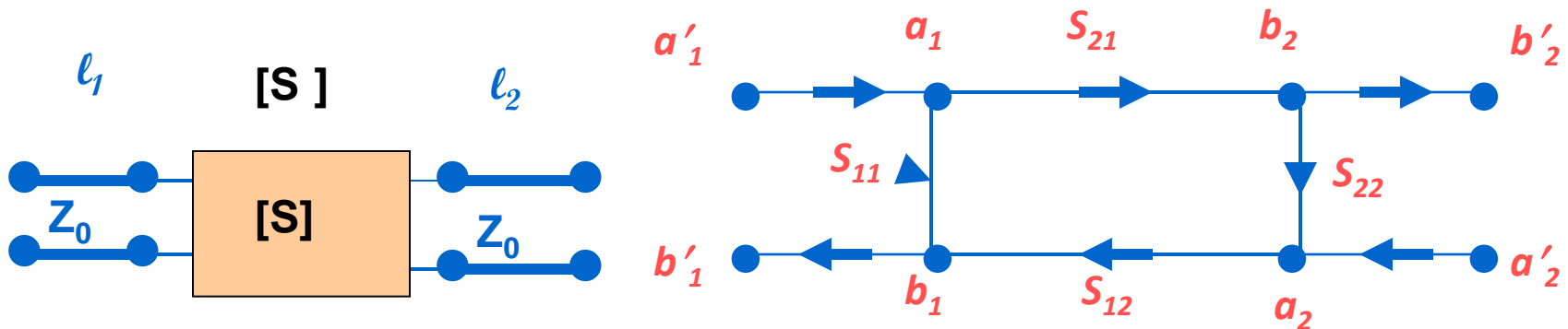
$$S_{22} = \left. \frac{b_2}{a_2} \right|_{a_1=0}$$

: reflection coefficient at port 2 with port 1 matched

IL or power gain from port 1 to port 2 $= -10 \log |S_{21}|^2$

IL or power gain from port 2 to port 1 $= -10 \log |S_{12}|^2$

RL at port 1 or port 2 $= -10 \log |S_{11}|^2$ **or** $= -10 \log |S_{22}|^2$



$$S'_{11} = S_{11}e^{-j2\beta l_1}, S'_{21} = S_{21}e^{-j2\beta(l_1+l_2)}$$

$$S'_{12} = S_{12}e^{-j2\beta(l_1+l_2)}, S'_{22} = S_{22}e^{-j2\beta l_2}$$

$$b_1 = a_1 S_{11} + a_2 S_{12}$$

$$b_2 = a_1 S_{21} + a_2 S_{22}$$

Reasons to use S-matrix in microwave circuit

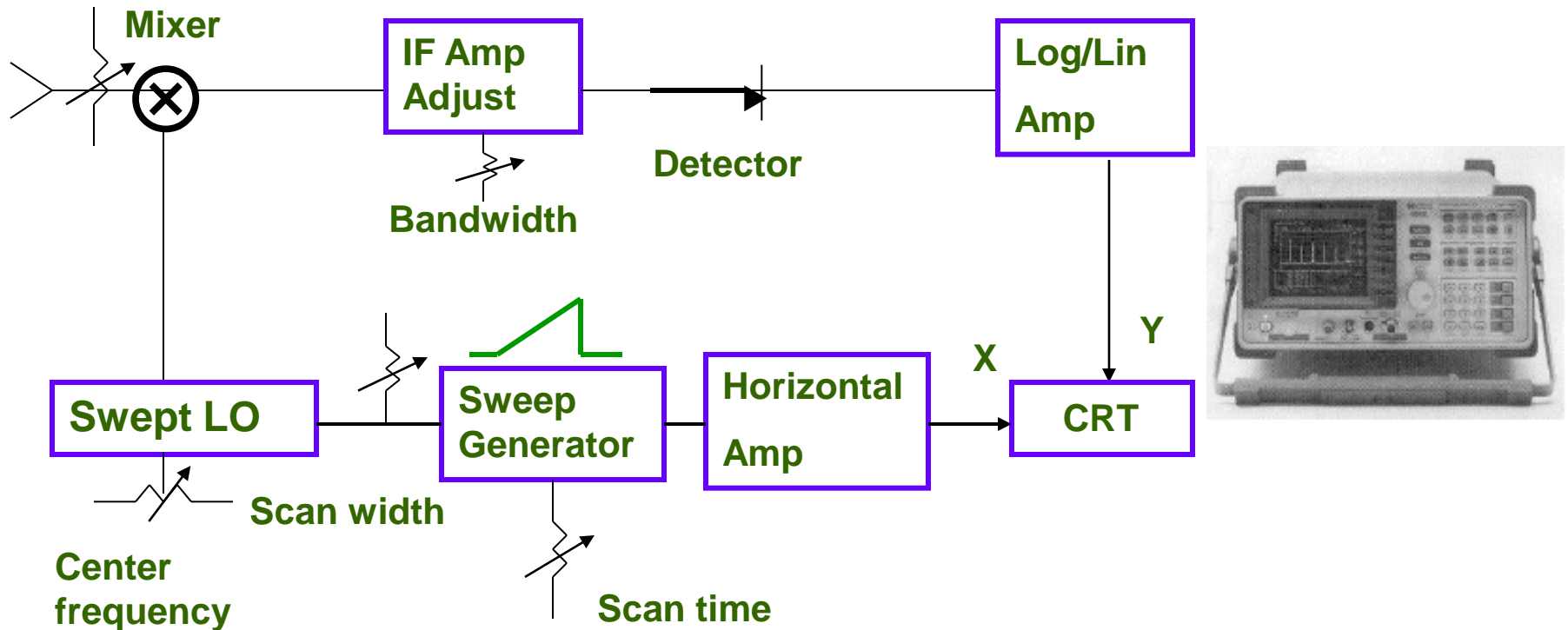
- (1) matched load available in broadband application
- (2) measurable quantity in terms of incident, reflected and transmitted waves
- (3) termination with Z_0 causes no oscillation
- (4) convenient to use in the microwave network analysis



Spectrum analyzer

Purpose: measure microwave signal spectrum, can also be used to measure frequency, rms voltage, power, distortion, noise power, amplitude modulation, frequency modulation, spectral purity,...

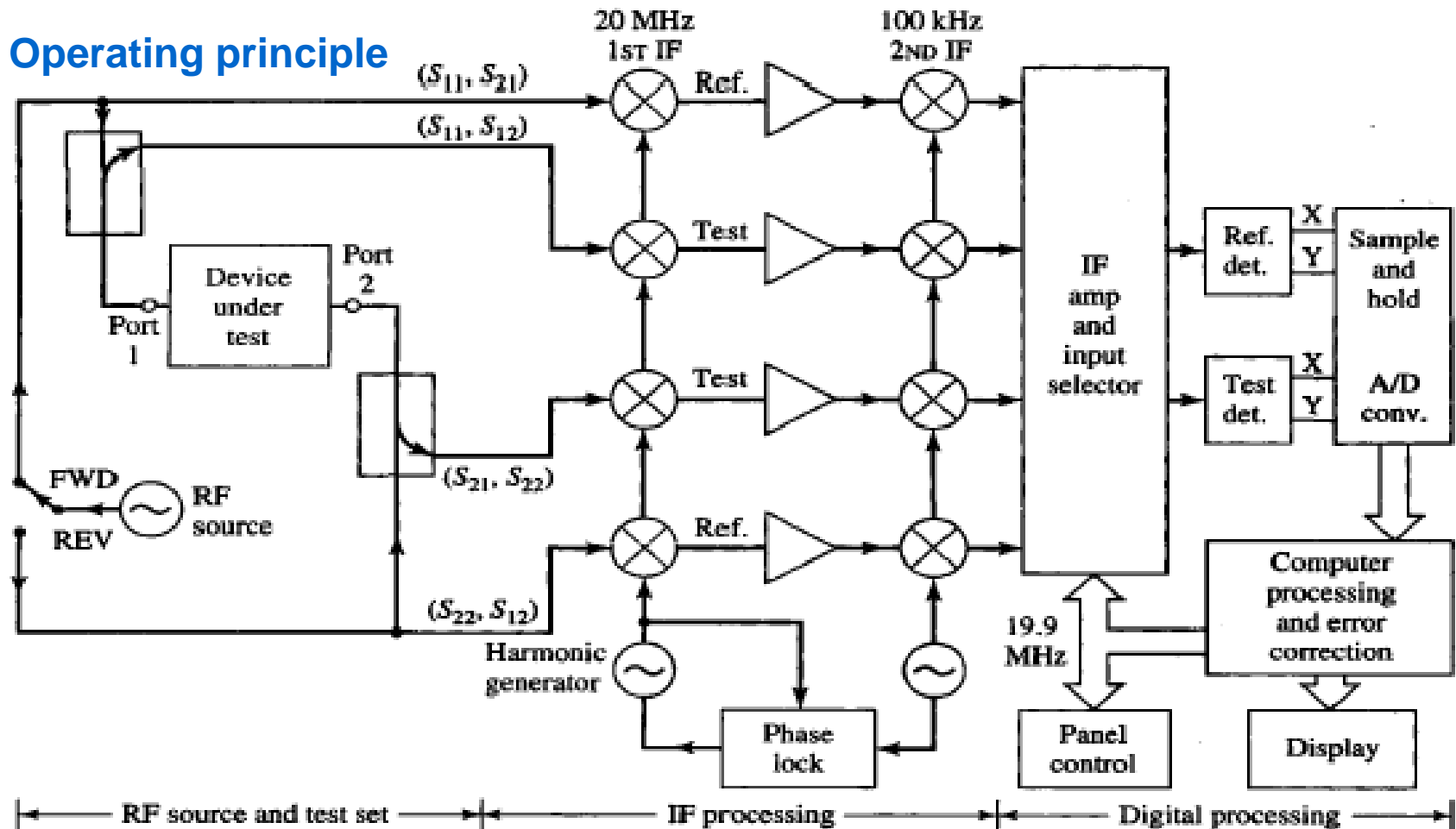
Operating principle





Purpose: measure two-port S-parameter of a microwave device or network, can also be used to measure VSWR, return loss, group delay, input impedance, antenna pattern, dielectric constant,....

Operating principle





Scalar network analyzer measures the magnitude of two-port S-parameters.

Hp8510 vector network analyzer

